
2SC1775, 2SC1775A

Silicon NPN Epitaxial

HITACHI

Application

- Low frequency low noise amplifier
- Complementary pair with 2SA872/A

Outline

TO-92 (1)



1. Emitter
2. Collector
3. Base

2SC1775, 2SC1775A

Absolute Maximum Ratings (Ta = 25°C)

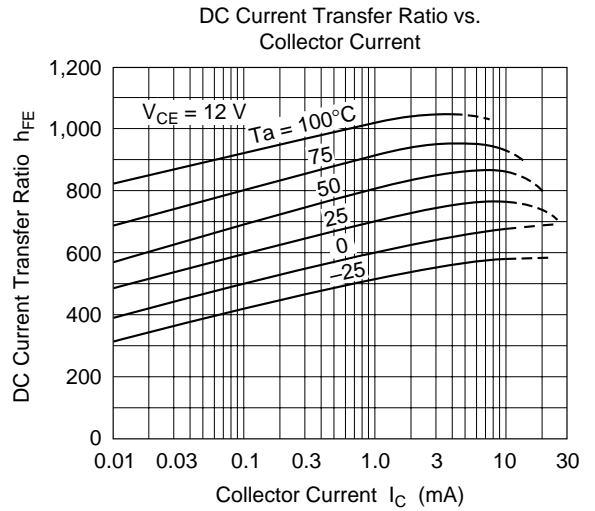
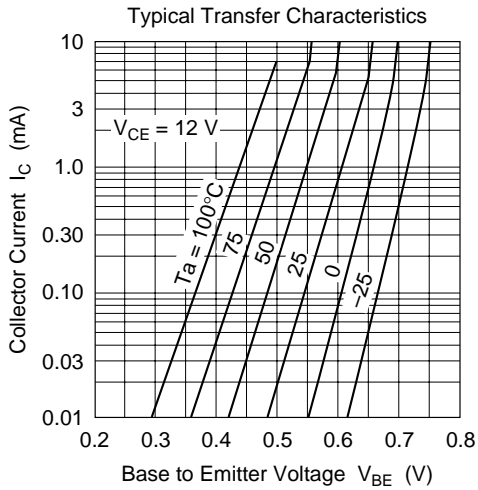
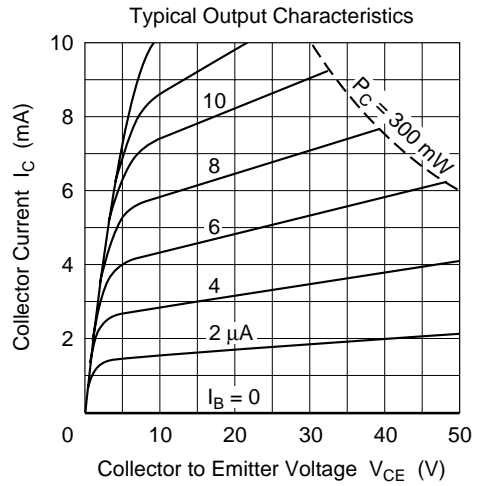
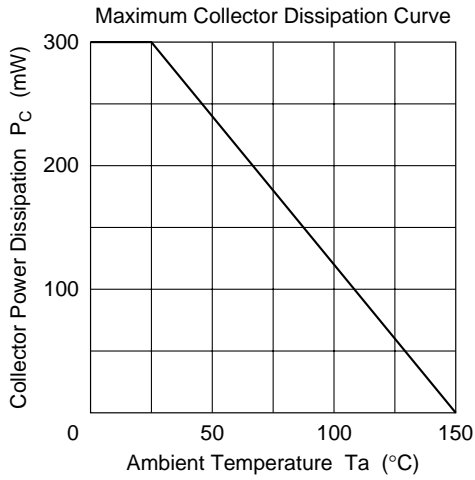
Item	Symbol	2SC1775	2SC1775A	Unit
Collector to base voltage	V_{CBO}	90	120	V
Collector to emitter voltage	V_{CEO}	90	120	V
Emitter to base voltage	V_{EBO}	5	5	V
Collector current	I_C	50	50	mA
Collector power dissipation	P_C	300	300	mW
Junction temperature	T_j	150	150	°C
Storage temperature	T_{stg}	-55 to +150	-50 to +150	°C

Electrical Characteristics (Ta = 25°C)

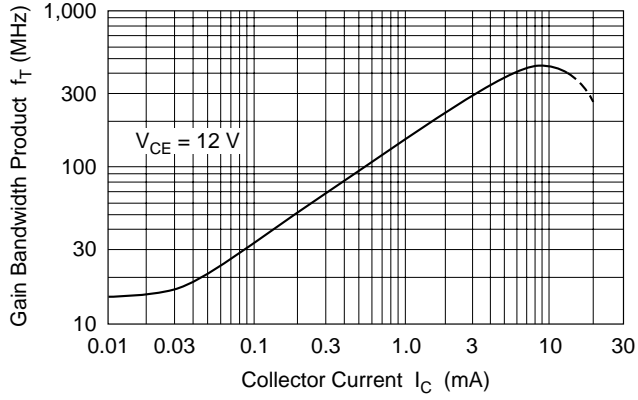
Item	Symbol	2SC1775			2SC1775A			Unit	Test conditions	
		Min	Typ	Max	Min	Typ	Max			
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	90	—	—	120	—	—	V	$I_C = 1 \text{ mA}$, $R_{BE} = \infty$	
Collector cutoff current	I_{CBO}	—	—	0.5	—	—	—	μA	$V_{CB} = 75 \text{ V}$, $I_E = 0$	
		—	—	—	—	—	0.5	μA	$V_{CB} = 100 \text{ V}$, $I_E = 0$	
DC current transfer ratio	h_{FE1}^{*1}	400	—	1200	400	—	1200		$V_{CE} = 12 \text{ V}$, $I_C = 2 \text{ mA}$	
	h_{FE2}	160	—	—	160	—	—		$V_{CE} = 12 \text{ V}$, $I_C = 0.1 \text{ mA}$	
Base to emitter voltage	V_{BE}	—	—	0.75	—	—	0.75	V	$V_{CE} = 12 \text{ V}$, $I_C = 2 \text{ mA}$	
Collector to emitter saturation voltage	$V_{CE(sat)}$	—	—	0.5	—	—	0.5	V	$I_C = 10 \text{ mA}$, $I_B = 1 \text{ mA}$	
Gain bandwidth product	f_T	—	200	—	—	200	—	MHz	$V_{CE} = 12 \text{ V}$, $I_C = 2 \text{ mA}$	
Collector output capacitance	C_{ob}	—	1.6	—	—	1.6	—	pF	$V_{CB} = 25 \text{ V}$, $I_E = 0$, $f = 1 \text{ MHz}$	
Noise figure	NF	—	—	5.0	—	—	5.0	dB	$V_{CE} = 6 \text{ V}$, $I_C = 50 \mu\text{A}$, $R_g = 50 \text{ k}\Omega$	$f = 10 \text{ Hz}$
		—	—	1.5	—	—	1.5	dB		$f = 1 \text{ kHz}$

Note: 1. The 2SC1775/A is grouped by h_{FE1} as follows.

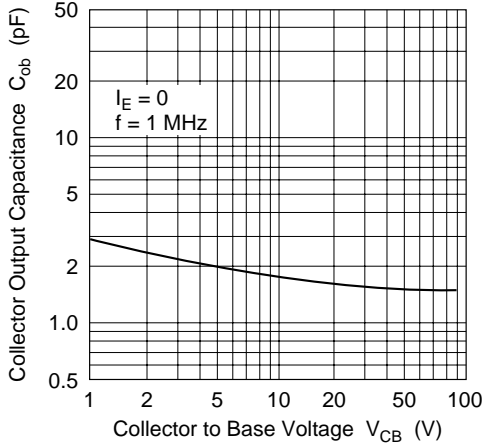
E	F
400 to 800	600 to 1200



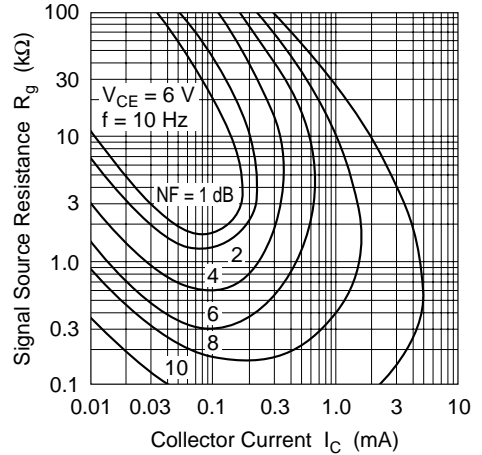
Gain Bandwidth Product vs. Collector Current

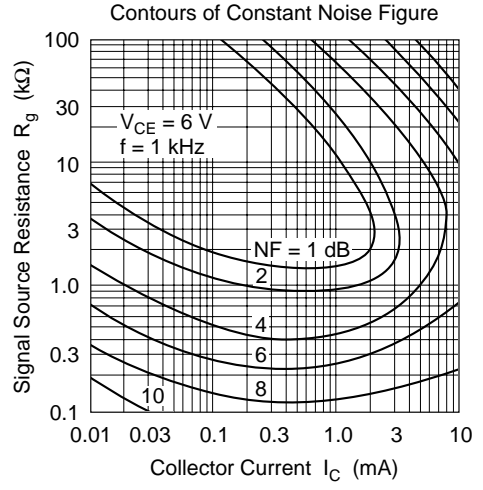
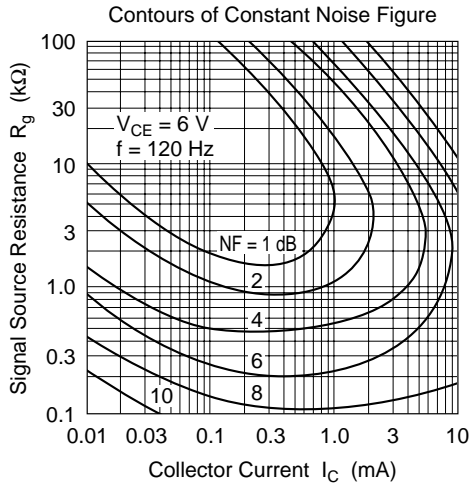


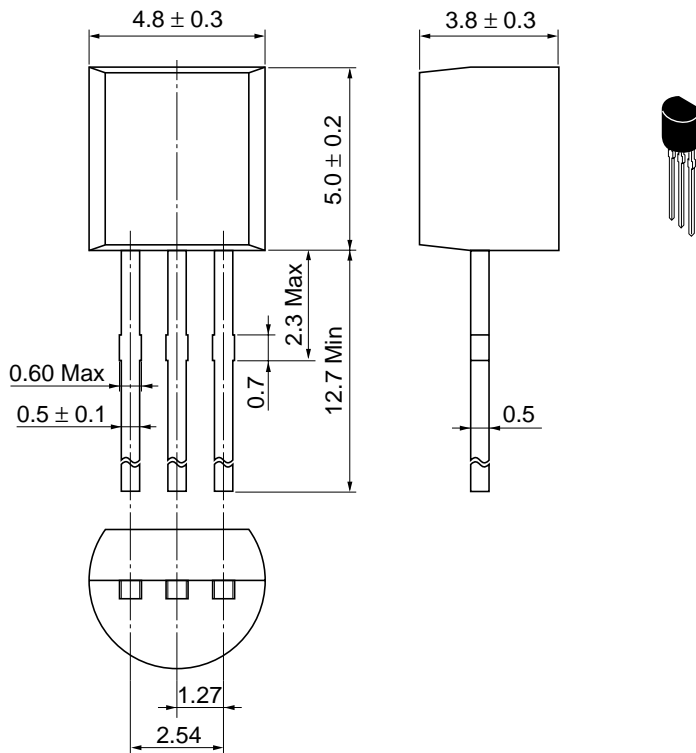
Collector Output Capacitance vs. Collector to Base Voltage



Contours of Constant Noise Figure







Hitachi Code	TO-92 (1)
JEDEC	Conforms
EIAJ	Conforms
Weight (reference value)	0.25 g

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HITACHI

Hitachi, Ltd.

Semiconductor & Integrated Circuits.
Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100-0004, Japan
Tel: Tokyo (03) 3270-2111 Fax: (03) 3270-5109

URL North America : <http://semiconductor.hitachi.com/>
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For further information write to:

Hitachi Semiconductor
(America) Inc.
179 East Tasman Drive,
San Jose, CA 95134
Tel: <1> (408) 433-1990
Fax: <1>(408) 433-0223

Hitachi Europe GmbH
Electronic components Group
Dornacher Straße 3
D-85622 Feldkirchen, Munich
Germany
Tel: <49> (89) 9 9180-0
Fax: <49> (89) 9 29 30 00

Hitachi Europe Ltd.
Electronic Components Group.
Whitebrook Park
Lower Cookham Road
Maidenhead
Berkshire SL6 8YA, United Kingdom
Tel: <44> (1628) 585000
Fax: <44> (1628) 778322

Hitachi Asia Pte. Ltd.
16 Collyer Quay #20-00
Hitachi Tower
Singapore 049318
Tel: 535-2100
Fax: 535-1533

Hitachi Asia Ltd.
Taipei Branch Office
3F, Hung Kuo Building, No.167,
Tun-Hwa North Road, Taipei (105)
Tel: <886> (2) 2718-3666
Fax: <886> (2) 2718-8180

Hitachi Asia (Hong Kong) Ltd.
Group III (Electronic Components)
7/F., North Tower, World Finance Centre,
Harbour City, Canton Road, Tsim Sha Tsui,
Kowloon, Hong Kong
Tel: <852> (2) 735 9218
Fax: <852> (2) 730 0281
Telex: 40815 HITEC HX

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